

N-channel 40 V 3.0 mΩ logic level MOSFET in LFPAK56

11 November 2014

Product data sheet

1. General description

Logic level N-channel MOSFET in LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lighting and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qu	ick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	194	W
Static charac	teristics						
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>		-	2.47	3	mΩ
Dynamic characteristics							
Q _{GD}	gate-drain charge	V _{GS} = 5 V; I _D = 25 A; V _{DS} = 32 V; Fig. 13; Fig. 14		-	10.7	-	nC

[1] Continuous current is limited by package.

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UT 4
4	G	gate	មុច្ចថ្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK9Y3R0-40E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9Y3R0-40E	93E040

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	40	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	40	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		$T_j \le 175 \ ^{\circ}C; Pulsed$	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	194	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u>	[3]	-	100	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>	[3]	-	100	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	718	А

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Symbol	Parameter	Conditions		Min	Мах	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C	[3]	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	718	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} & {\sf I}_{\sf D} = 100 \; {\sf A}; {\sf V}_{sup} \le 40 \; {\sf V}; {\sf R}_{\sf GS} = 50 \; \Omega; \\ & {\sf V}_{\sf GS} = 5 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; {}^\circ{\sf C}; \; unclamped; \\ & {\sf Fig. 4} \end{split}$	[4][5]	-	193.8	mJ

- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering $\rm T_{j}$ and or $\rm V_{GS}$ [1]
- [2]
- Continuous current is limited by package. [3]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [4]
- [5] Refer to application note AN10273 for further information.

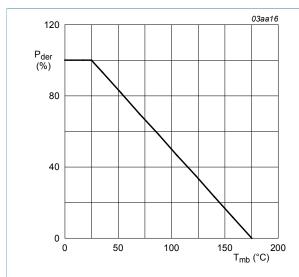
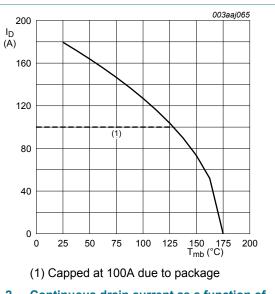
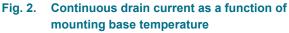


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

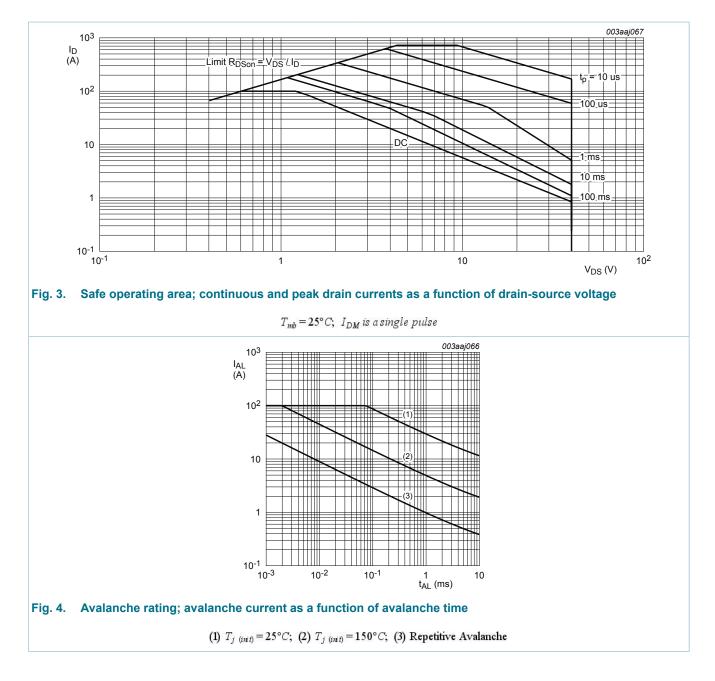




 $V_{GS} \ge 5V$

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9. Thermal characteristics

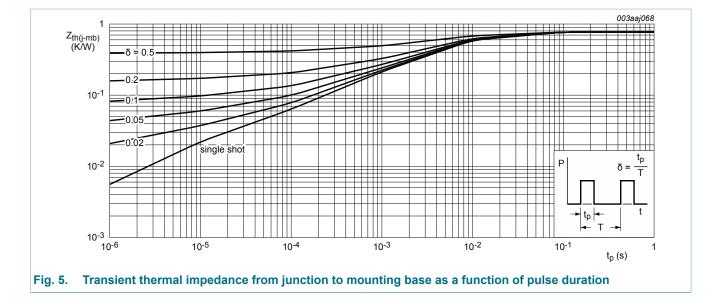
Table 6. The	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.77	K/W

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10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · ·	I			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	40	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	36	-	-	V
V _{GS(th)}	gate-source threshold voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; Fig. 9; Fig. 10	$V_{GS} = 0 \ V; T_j = -55 \ ^{\circ}C$ 36- $DS = V_{GS}; T_j = 25 \ ^{\circ}C;$ 1.41.72.1 $D_{DS} = V_{GS}; T_j = -55 \ ^{\circ}C;$ 2.4 $DS = V_{GS}; T_j = 175 \ ^{\circ}C;$ 0.5 $V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$ -0.1310 $V_{GS} = 0 \ V; T_j = 175 \ ^{\circ}C$ 500 $V_{DS} = 0 \ V; T_j = 25 \ ^{\circ}C$ -2100 $v_{DS} = 0 \ V; T_j = 25 \ ^{\circ}C$ -2100 $v_{DS} = 0 \ V; T_j = 25 \ ^{\circ}C;$ -2100 $v_{DS} = 0 \ V; T_j = 25 \ ^{\circ}C;$ -2100 $v_{DS} = 0 \ V; T_j = 25 \ ^{\circ}C;$ -2100 $v_{DS} = 0 \ V; T_j = 25 \ ^{\circ}C;$ -2100 $v_{DS} = 0 \ V; T_j = 25 \ ^{\circ}C;$ -2100 $v_{DS} = 25 \ A; T_j = 25 \ ^{\circ}C;$ -1.982.5 $v_{D} = 25 \ A; T_j = 175 \ ^{\circ}C;$ 6	2.1	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9	0.5	-	-	V	
I _{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C	-		μA	
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	- .13 10 500 100 .47 3 .98 2.5	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	- - 1.7 2.1 1.7 2.45 - 2.45 - - 0.13 10 - 500 2 100 2.47 3 1.98 2.5 - 6 35.5 -	nA	
R _{DSon}	drain-source on-state	V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 11</u>	$= 10 \text{ V}; \text{ V}_{\text{DS}} = 0 \text{ V}; \text{ T}_{\text{j}} = 25 \text{ °C} \qquad - \qquad 2 \qquad 10$ $= -10 \text{ V}; \text{ V}_{\text{DS}} = 0 \text{ V}; \text{ T}_{\text{j}} = 25 \text{ °C} \qquad - \qquad 2 \qquad 10$	3	mΩ	
resistan	resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	1.98	2.5	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	6	mΩ
Dynamic cł	naracteristics		1		1	
Q _{G(tot)}	total gate charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 5 V;	-	35.5	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	11.7	-	nC

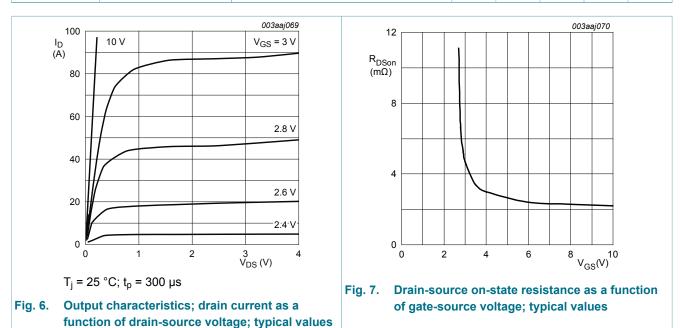
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{GD}	gate-drain charge		-	10.7	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	4471	5962	pF
C _{oss}	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; \text{ f} = 1 \text{ MHz};$ $T_{j} = 25 \text{ °C}; \underline{Fig. 15}$ $V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; \text{ V}_{GS} = 5 \text{ V};$ $R_{G(ext)} = 5 \Omega$	 -	563	676	pF
C _{rss}	reverse transfer capacitance		-	251	344	pF
t _{d(on)}	turn-on delay time		-	24	-	ns
t _r	rise time		-	44	-	ns
t _{d(off)}	turn-off delay time		-	53	-	ns
t _f	fall time	_	-	34	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>	-	0.81	1.2	V
t _{rr}	reverse recovery time	I_{S} = 20 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;	-	30	-	ns
Qr	recovered charge	$R_{G(ext)} = 5 \Omega$ $I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; Fig. 16$	-	25	-	nC

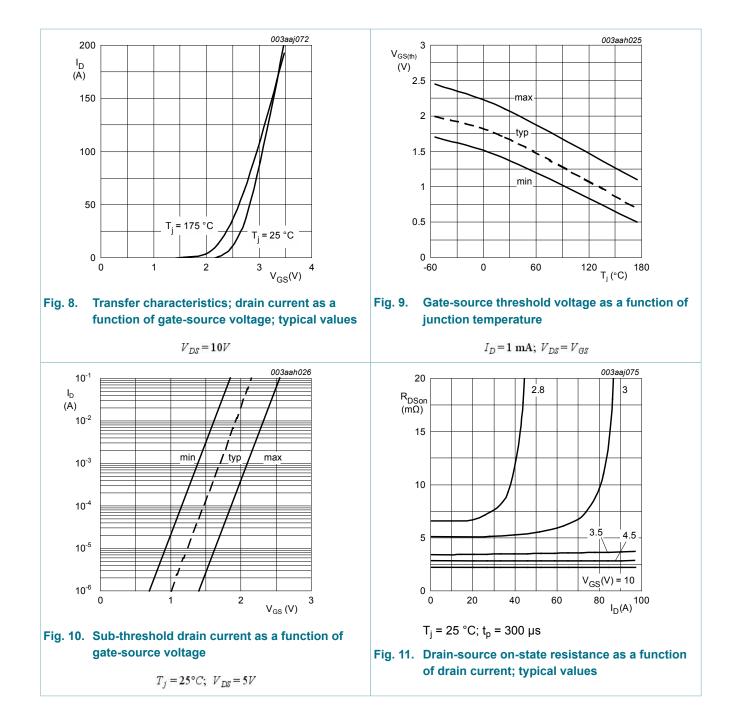


 $T_j = 25^{\circ}C; \ I_D = 25A$

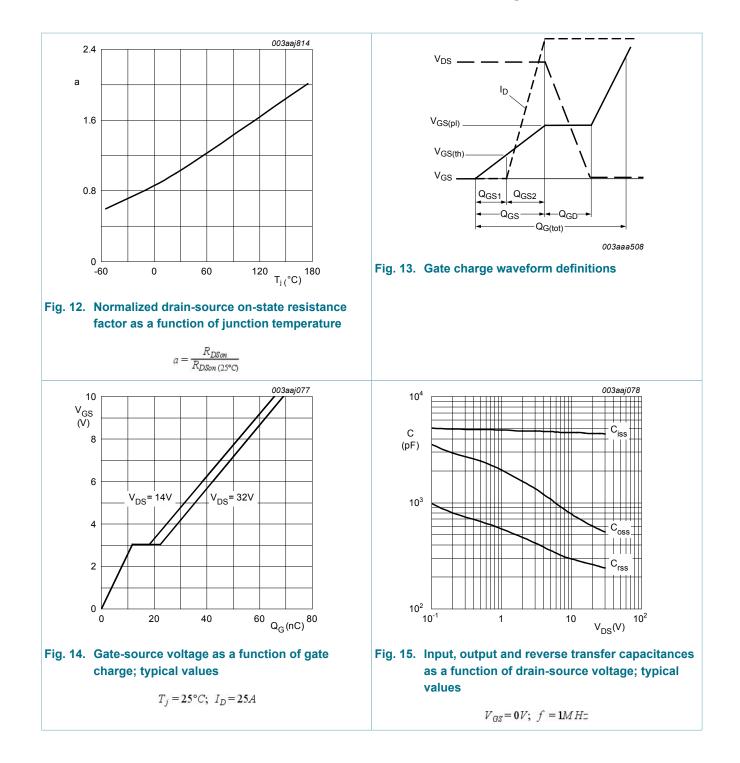
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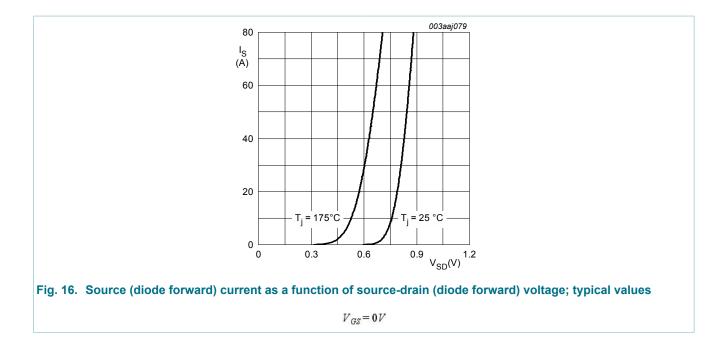


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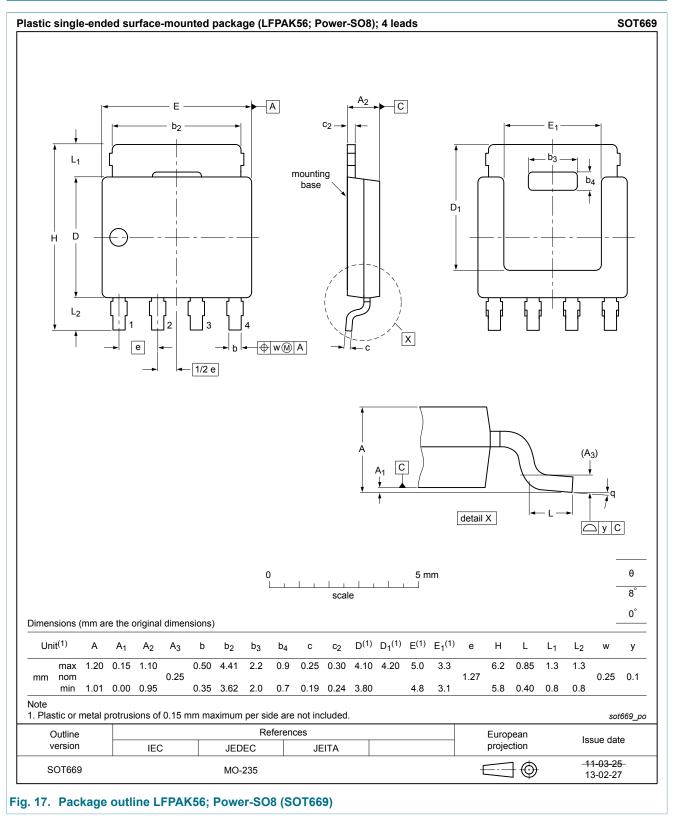
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11. Package outline



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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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	Features and benefits

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